Tatsuya Yasuoka

List of Publications by Year in descending order

Source: https://exaly.com/author-pdf/1526722/publications.pdf

Version: 2024-02-01

		1684188	1588992
8	131	5	8
papers	citations	h-index	g-index
8	8	8	148
all docs	docs citations	times ranked	citing authors

#	Article	IF	CITATIONS
1	Optical Characterization of Gallium Oxide \hat{l}_{\pm} and \hat{l}_{2} Polymorph Thin-Films Grown on c-Plane Sapphire. Journal of Electronic Materials, 2021, 50, 2990-2998.	2.2	9
2	The effect of HCl on the \hat{l}_{\pm} -Ga2O3 thin films fabricated by third generation mist chemical vapor deposition. AIP Advances, 2021, 11, 045123.	1.3	7
3	Sub- \hat{l} ¹ /4m features patterned with laser interference lithography for the epitaxial lateral overgrowth of \hat{l} ±-Ga2O3 via mist chemical vapor deposition. Applied Physics Letters, 2021, 119, 041902.	3.3	6
4	\hat{l}_{\pm} -(AlxGa1â^x)2O3 single-layer and heterostructure buffers for the growth of conductive Sn-doped \hat{l}_{\pm} -Ga2O3 thin films via mist chemical vapor deposition. APL Materials, 2020, 8, .	5.1	15
5	Conductive Si-doped α-(AlxGa1â^'x)2O3 thin films with the bandgaps up to 6.22 eV. AIP Advances, 2020, 10, 115019.	1.3	13
6	Challenges of fabrication of a large-area-uniform molybdenum disulfide layered thin film at low growth temperature by atmospheric-pressure solution-based mist CVD. Japanese Journal of Applied Physics, 2018, 57, 110306.	1.5	6
7	Growth of α-Cr2O3 single crystals by mist CVD using ammonium dichromate. Applied Physics Express, 2018, 11, 111101.	2.4	11
8	Bandgap engineering of \hat{l}_{\pm} -(AlxGa1-x)2O3 by a mist chemical vapor deposition two-chamber system and verification of Vegard's Law. Applied Physics Letters, 2018, 113, .	3.3	64